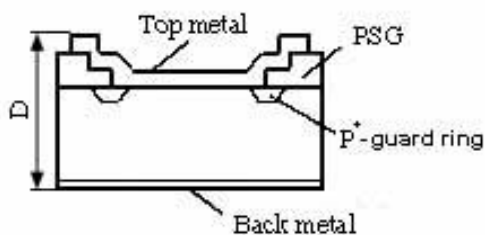
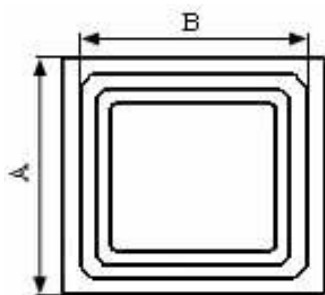


		0,2A/30V. Die Size-13mil.		
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	$V_{BR}$	V	30	35
Average Rectified Forward Current	$I_{F(AV)}$	mA	200	-
DC Forward Voltage @ $25^\circ\text{C}$ , $I_F=0,2\text{A}$	$V_F$	V	0,52	0,5
Maximum Reverse Current @ $25^\circ\text{C}$ , $V_R=30\text{V}$ @ $125^\circ\text{C}$ , $V_R=30\text{V}$	$I_R$	mA	0,08 8,0	0,05 5,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}^*$	A	5	-
Peak Repetitive Reverse Surge Current @ $2,0\mu\text{s}$ , $f=1\text{kHz}$ ., $T_j<175^\circ\text{C}$ .	$I_{RRM}$	A	0,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	$V_{ESD}$	kV	$\pm 4$ (contact)	
Diode capacitance $V_r=0\text{V}$ , $f=1\text{MHz}$	$C_j$	pf	30	
Voltage Rate of Change	$dV/dt$	$\text{V}/\mu\text{S}$	10.000	
Operating Junction Temperature	$T_j^{**}$	$^\circ\text{C}$	150	

\* - testing for Device

\*\* -  $T_j = T_a + R_{th}(j-a) \times (P_f + P_r)$ , where  $R_{th}(j-a)$  – thermal resistance,  $P_f$  – forward power dissipation,  $P_r$  – revers power dissipation



DIM	ITEM	$\mu\text{m}$
$A_x$ $A_y$	Wafer Form Die Size	330 330
$B_x$ $B_y$	Top Metal Size	185 185
D	Thickness	200max.
Scribe line Width		80

*Top metal:*

- a) **Al-Ni-Ag** – for Soldering;
- b) **Al** – for Wire Bonding.

Backside metal: **Ti-Ni-Ag**.